

SAMSUNG SEMICONDUCTOR INC 14E D 7964142 0006926 7 T-31-23

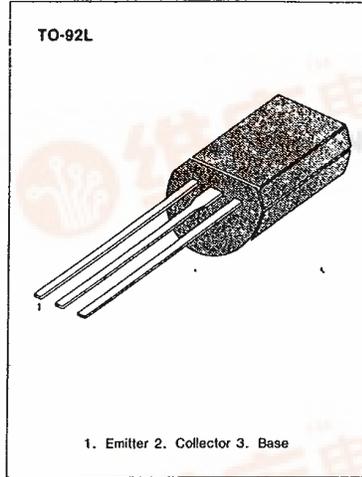
KSC2340 NPN EPITAXIAL SILICON TRANSISTOR

COLOR TV CHROMA OUTPUT

- Collector-Base Voltage $V_{CBO}=350V$
- Current Gain-Bandwidth Product $f_T=50MHz$ (Typ)

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	350	V
Collector-Emitter Voltage	V_{CEO}	350	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector Current	I_C	100	mA
Collector Dissipation	P_C	1	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{stg}	-55 ~ 150	$^\circ C$



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

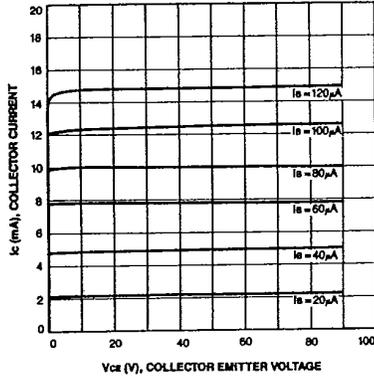
Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=100\mu A, I_E=0$	350			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=5mA, I_B=0$	350			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=-100\mu A, I_C=0$	7			V
Collector Cutoff Current	I_{CBO}	$V_{CB}=200V, I_E=0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=10V, I_C=20mA$	30		150	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$			0.5	V
Current Gain Bandwidth Product	f_T	$V_{CE}=10V, I_C=20mA$	50			MHz
Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		8		pF



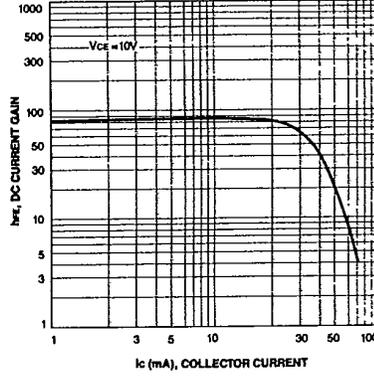
KSC2340

NPN EPITAXIAL SILICON TRANSISTOR

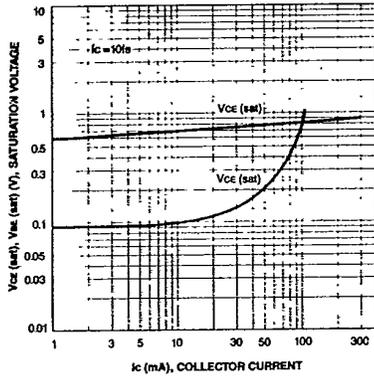
STATIC CHARACTERISTIC



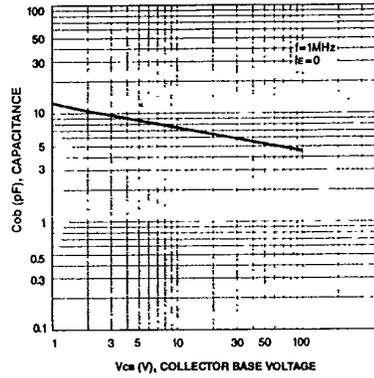
DC CURRENT GAIN



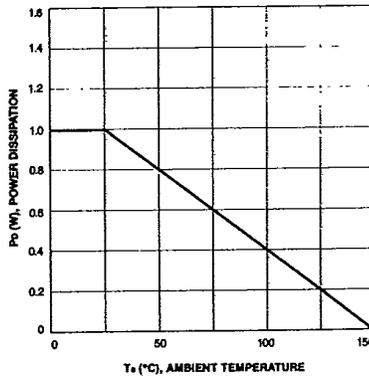
**BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE**



COLLECTOR OUTPUT CAPACITANCE



POWER DERATING



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